

STESB01

ESBT Base Driver

Feature summary

- Controls ESBT base current in every line/load condition
- Supply voltage range: 8V to 20 V
- Storage time controlled by closed loop architecture (from 150ns to 1.5µs)
- Under voltage lockout with hysteresis

Description

The STESB01 is a dedicated base current biasing transistor for the Emitter-Switched Bipolar Transistor (ESBT) family of power switches. The device is able to control the ESBT storage time (from 150ns to 1.5is) using closed loop architecture. This guarantees proper operation of the ESBT in every line and load condition, avoiding oversaturation of the device and, at the same time, ensuring the correct base current



when a higher load is required. The storage time can be adjusted with an external resistor, which allows maximum flexibility in different applications.

The optimization of the base current value also reduces the base current losses to minimum level.

Order code

Part number	Package	Packaging
STESB01STR	SOT23-6L	3000 Parts per Reel
STESB01DR	SO-8	2500 Parts per Reel

October 2006

Contents

1	Schematic diagram
2	Pin configuration
3	Maximum ratings
4	Electrical characteristics
5	Diagram
6	Package mechanical data 8
7	Revision history



1 Schematic diagram

Figure 1. Schematic diagram



2 Pin configuration

Figure 2. Pin Connections (Top View)



Table 1. Pin description

Pin N° for SO-8	Pin N° for SOT23	Symbol	Name and function
8	1	DRIVE	This is the base current driver for the external PNP transistor (see Application Schematic) which determines the ESBT base current value.
6, 7	2	GND	Ground. Reference for all the signal of the IC.
5	3	STG _{ADJ}	Adjustable Storage (adjusted by connecting a resistor between this pin and GND pin). A minimum value of 150ns can be achieved with $10k\Omega$ resistor. See note 4.
4	4	V _{COLL}	Collector Voltage. This pin must be connected to the ESBT collector through a resistor divider. The rising edge of this signal provides end-of-storage time information.
2	5	PWM	Pulse Width Modulation. This pin must be connected to the PWM controller output. The falling edge of this signal provides beginning-of-storage time information.
1	6	V _{CC}	Supply Voltage. It range is from 8V to 20V. A ceramic Bypass capacitor must be connected between V_{CC} and GND.
3		N.C.	Not Connected.



3 Maximum ratings

Table 2.Absolute maximum ratings

Symbol	Parameter	Value	Unit
V _{CC}	DC Input voltage	-0.3 to 22	V
Drive	Drive output voltage	-0.3 to V _{CC}	V
STG _{ADJ}	Storage time adjust voltage	-0.3 to 5	V
PWM	PWM Input voltage	-0.3 to 15	V
V _{COLL}	Collector input voltage	-0.6 to 5	V
ESD	Human body model	+2	kV
P _{TOT}	Continuous power dissipation (at $T_A = 105^{\circ}C$)	TBD	mW
T _{STG}	Storage temperature range	-40 to 150	°C
T _{OP}	Operating junction temperature range	-40 to 125	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied.

Table 3. Thermal data

Symbol	Parameter	SOT23-6L	SO-8	Unit
R _{thJC}	Thermal resistance junction-case	81	20	°C/W
R _{thJA}	Thermal resistance junction-ambient	255	55	°C/W

This value is referred to 1 layer PCB board with minimum copper connections for the leads.



4 Electrical characteristics

Table 4. Electrical characteristics

(V_{CC} = 20V, C_I = 3.3μ F, T_J= -40° C to 125° C unless otherwise specified.)

Symbol	Parameter	Test Conditions		Тур.	Max.	Unit	
Supply Input and Under Voltage Lock Out							
Vee	Turn On Threshold	V _{CC} rising		7.5	8	V	
V CC	Turn Off Threshold after Turn On	V _{CC} falling	6.5	7		v	
lee	Supply Current	PWM=V _{COLL} =0V		2		mA	
100	Supply Surrent	See Note 1		2		IIIA	
Driver Outp	out (T _J = 27°C)						
V _{OL}	Low Level Voltage	I _{DRIVE} =10mA		50		mV	
	Drive Current in open loop	V_{DRIVE} = 1.25V, R_{STGadj} =150 k Ω	0.25			Δ	
'DRIVE(OL)		See Note 2, Note 4		0.20		~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~	
Storage Co	ontrol						
V _{PWML}	PWM Low Level Threshold	See Note 3			1.5	V	
V _{PWMH}	PWM High Level Threshold	See Note 3	3.5			V	
I _{PWM}	PWM input bias current	PWM = 0V to 15V	-0.1		0.1	μA	
V _{COLL(L)}	Collector Low Level Threshold	See Note 3			0.8	V	
V _{COLL(H)}	Collector High Level Threshold	See Note 3	2.5			V	
I _{COLL}	V _{COLL} input bias current	V _{COLL} = 0V to 5V	-0.1		0.1	μA	

1 To the PWM pin must be applied a 5V to 0V falling edge while the voltage level on the V_{COLL} pin must be 0V. After 300 ns, to the V_{COLL} pin must be applied a 0V to 5V rising edge. The maximum frequency of signals applied to PWM and V_{COLL} pins must be 300 kHz.

- 2 To the PWM pin must be applied a 5V to 0V falling edge while the voltage level on the V_{COLL} pin must be 0V. After 200 ns, to the V_{COLL} pin must be applied a 0V to 5V raising edge. The maximum frequency of signals applied to PWM and V_{COLL} pins must be 300 kHz.
- 3 Guaranteed by Design.
- 4 In parallel to the resistor a low-leakage/low-ESR capacitor could be necessary for bypassing purpose.



5 Diagram





Figure 4. Typical operating characteristics



6 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK[®] packages. These packages have a Lead-free second level interconnect. The category of second Level Interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com.



		mm.			mils		
DIM.	MIN.	ТҮР	MAX.	MIN.	TYP.	MAX.	
А	0.90		1.45	35.4		57.1	
A1	0.00		0.15	0.0		5.9	
A2	0.90		1.30	35.4		51.2	
b	0.35		0.50	13.7		19.7	
С	0.09		0.20	3.5		7.8	
D	2.80		3.00	110.2		118.1	
E	2.60		3.00	102.3		118.1	
E1	1.50		1.75	59.0		68.8	
е		0.95			37.4		
e1		1.9			74.8		
L	0.35		0.55	13.7		21.6	







57

	SO-8 MECHANICAL DATA					
DIM		mm.				
DIW.	MIN.	ТҮР	MAX.	MIN.	TYP.	MAX.
А	1.35		1.75	0.053		0.069
A1	0.10		0.25	0.04		0.010
A2	1.10		1.65	0.043		0.065
В	0.33		0.51	0.013		0.020
С	0.19		0.25	0.007		0.010
D	4.80		5.00	0.189		0.197
E	3.80		4.00	0.150		0.157
е		1.27			0.050	
Н	5.80		6.20	0.228		0.244
h	0.25		0.50	0.010		0.020
L	0.40		1.27	0.016		0.050
k			8° (r	nax.)		•
ddd			0.1			0.04



	Tape & Reel SOT23-xL MECHANICAL DATA					
DIM		mm.				
DIM.	MIN.	ТҮР	MAX.	MIN.	TYP.	MAX.
А			180			7.086
С	12.8	13.0	13.2	0.504	0.512	0.519
D	20.2			0.795		
Ν	60			2.362		
Т			14.4			0.567
Ao	3.13	3.23	3.33	0.123	0.127	0.131
Во	3.07	3.17	3.27	0.120	0.124	0.128
Ko	1.27	1.37	1.47	0.050	0.054	0.0.58
Po	3.9	4.0	4.1	0.153	0.157	0.161
Р	3.9	4.0	4.1	0.153	0.157	0.161



57

11/14

	Tape & Reel SO-8 MECHANICAL DATA					
	mm.			inch		
DIM.	MIN.	ТҮР	MAX.	MIN.	TYP.	MAX.
A			330			12.992
С	12.8		13.2	0.504		0.519
D	20.2			0.795		
N	60			2.362		
Т			22.4			0.882
Ao	8.1		8.5	0.319		0.335
Во	5.5		5.9	0.216		0.232
Ко	2.1		2.3	0.082		0.090
Po	3.9		4.1	0.153		0.161
Р	7.9		8.1	0.311		0.319



7 Revision history

Table 5.Revision history

Date	Revision	Changes
16-Nov-2005	1	Initial release.
26-Jul-2006	2	Mistake on table 3 function of pin 3.
03-Oct-2006	3	Add new package SO-8.



Please Read Carefully:

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

UNLESS EXPRESSLY APPROVED IN WRITING BY AN AUTHORIZED ST REPRESENTATIVE, ST PRODUCTS ARE NOT RECOMMENDED, AUTHORIZED OR WARRANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCTS OR SYSTEMS WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE. ST PRODUCTS WHICH ARE NOT SPECIFIED AS "AUTOMOTIVE GRADE" MAY ONLY BE USED IN AUTOMOTIVE APPLICATIONS AT USER'S OWN RISK.

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2006 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan -Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com

